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# ANTENNA-IN-PACKAGE CONCEPT FOR MMWAVE FRONT-END APPLICATIONS

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Fraunhofer IZM Serena Team  
[ivan.ndip@izm.fraunhofer.de](mailto:ivan.ndip@izm.fraunhofer.de)

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# Outline

- Challenges and Advantages of using mmWave Spectrum
- Package concept, substrate stack-up
- Material characterization
- Design of module and components
- Fabrication
- Measurement

# Challenges and Advantages when using mmWave / THz Spectrum

■ Bandwidth → Data rate  $C = BW \log_2(1 + SNR)$

■ High path loss

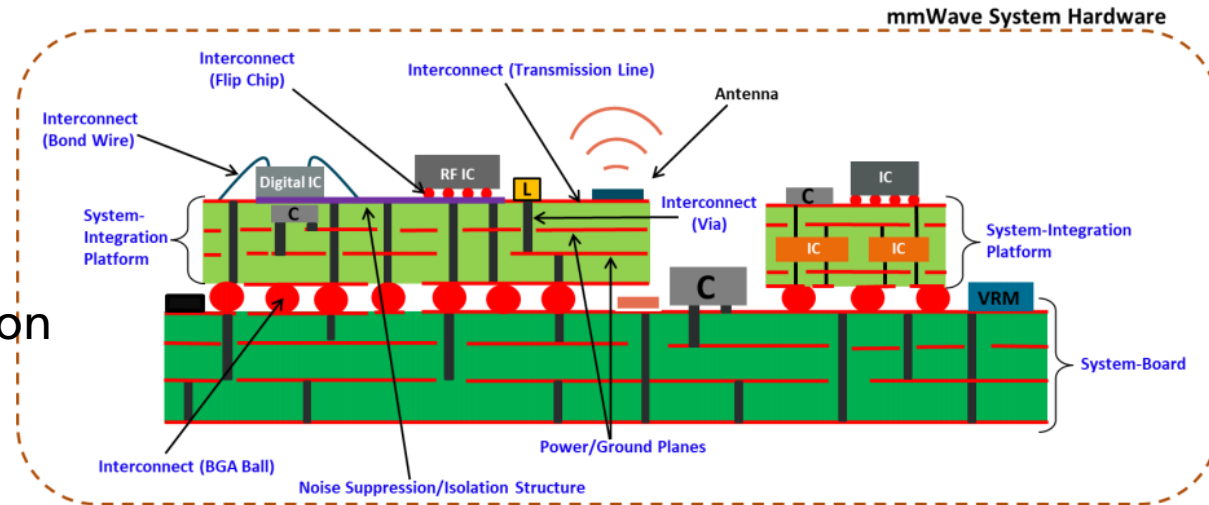
Frequency	3.5 GHz (n78)	39 GHz (n260)	140 GHz	300 GHz
Free Space Path Loss (300 m)	93 dB	114 dB (+21)	125 dB (+ 32)	132 dB (+ 39)

■ Additional loss due to atmospheric (e.g. rain) and blockage (e.g. cars)

■ Approach: mmWave and Beamforming using heterogeneous integration

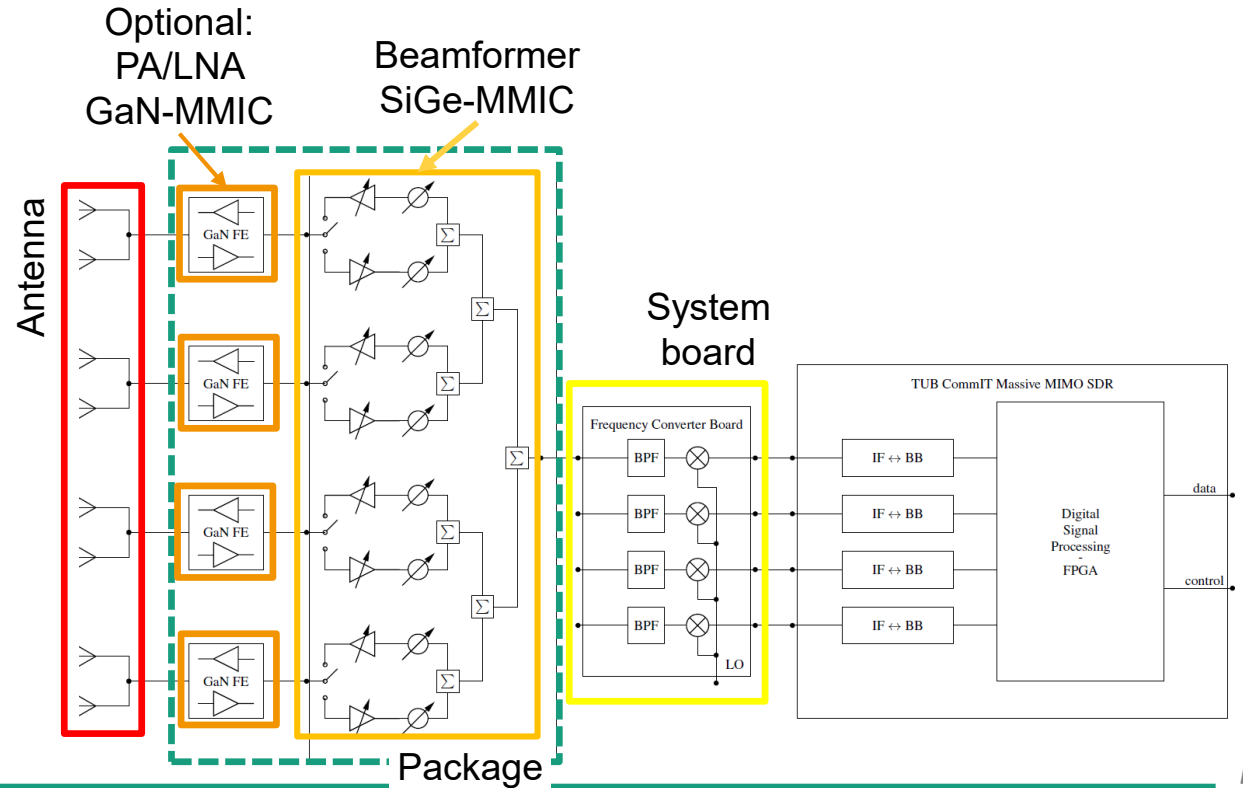
# Requirements for mmWave / THz Packaging and Antenna Integration

- Cost
- Performance / Functionality
  - Fabrication of high gain antennas  $G \sim D e_{Subst} e_{Cond} e_{Match}$
  - Intry-system EMC
  - Signal/Power Integrity
  - High Q Passives
- Functional Scablability
- Heterogeneous Integration
- Miniaturization



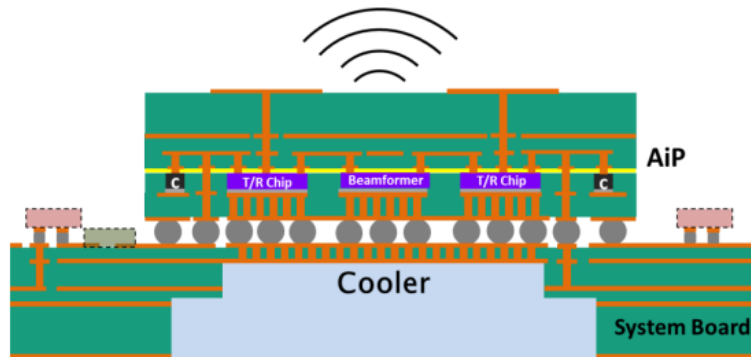
# Block Diagram

- Hybrid Beamforming demonstration system for 5G base stations
- Antenna-in package RF front-end
- Integration of
  - GaN PA/LNA
  - SiGe beamforming MMICs



# Package Concept

- PCB Embedding Antenna-in-Package module
- SiGe Beamforming IC 39 GHz + decoupling capacitors
- 6 metal layers
- Bottom layer with LGA Interface



European Patent Nr. EP3346548B1; US20180191062A1

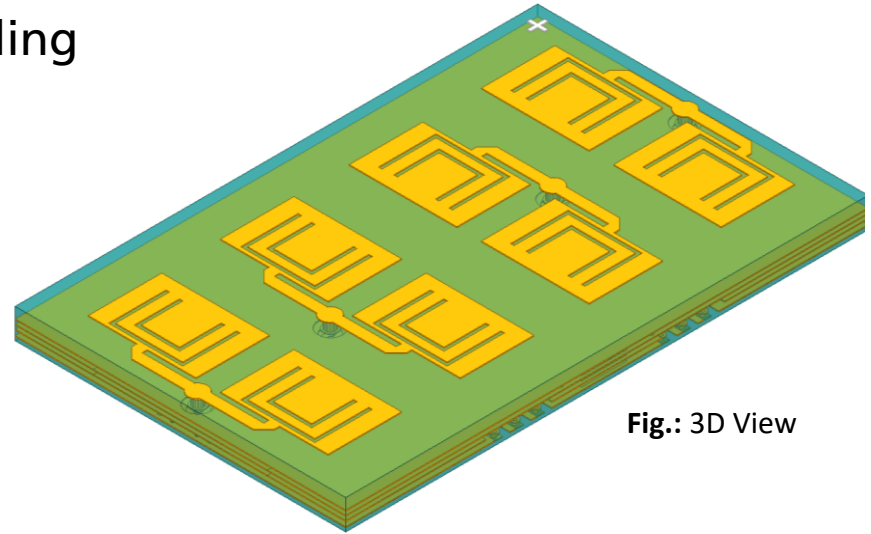
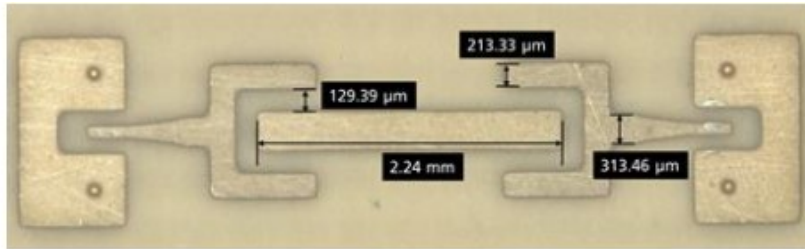


Fig.: 3D View

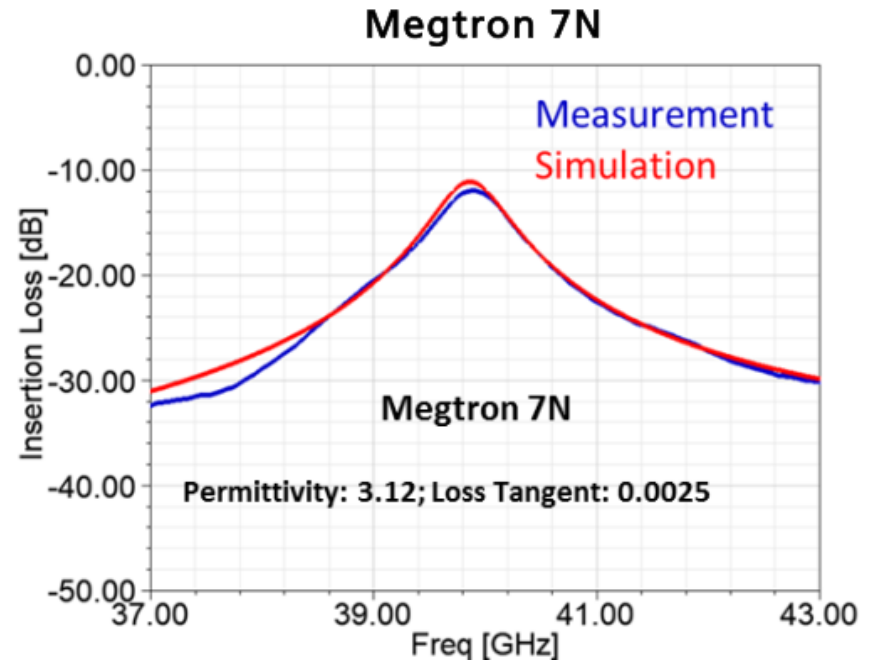
Fig.: Concept of SERNA module

# Dielectric Material Characterization

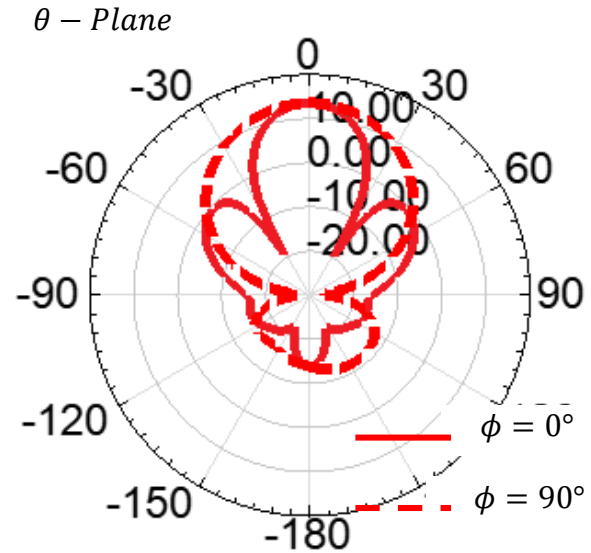
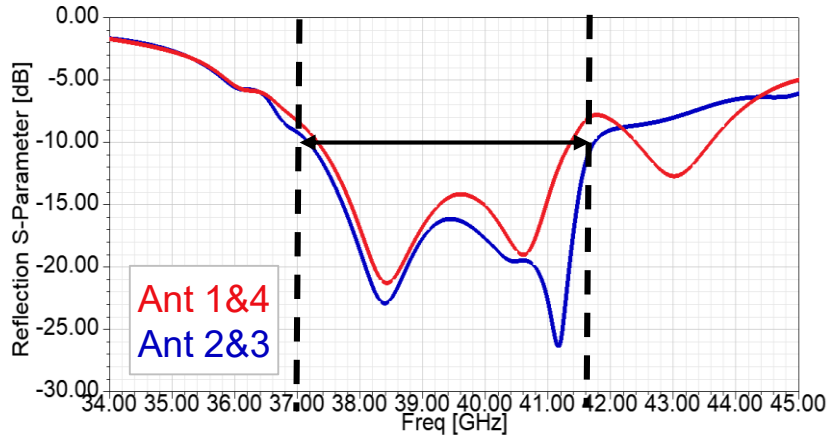
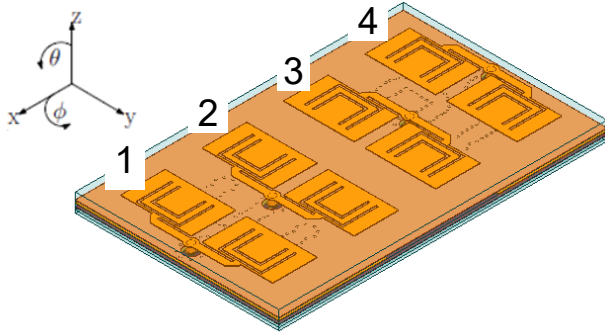
- Dielectric material characterization using planar resonators



Fabricated planar resonator for measuring relative dielectric constant and loss tangent of Megtron 7N substrate



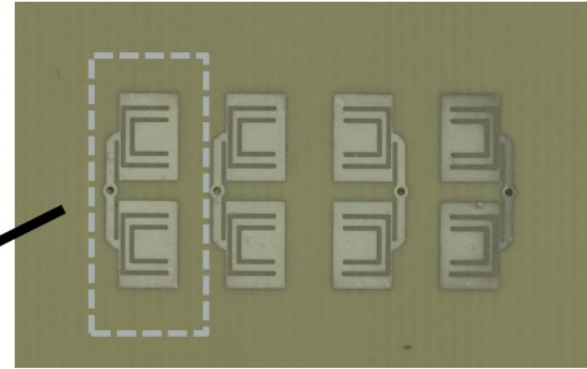
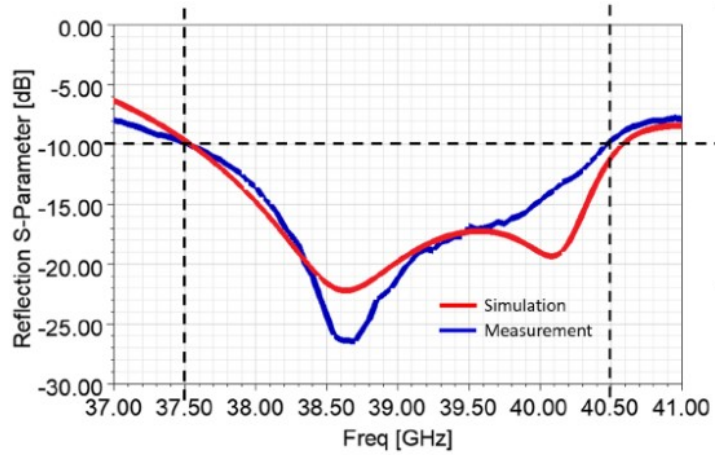
# Package Component Design - Antennas



- Antenna properties
- -10 dB bandwidth
  - Antenna 1&4: 4 GHz (37.3-41.3 GHz)
  - Antenna 2&3: 4.5 GHz (37.1-41.6 GHz)
- Realized gain (full array): 13.5dBi @ 38.5 GHz

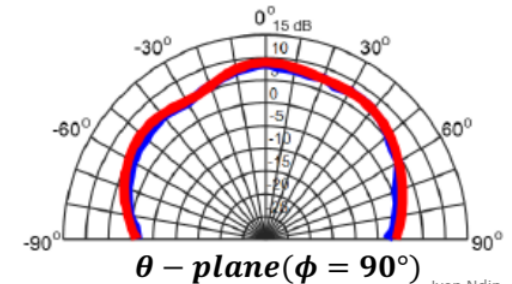
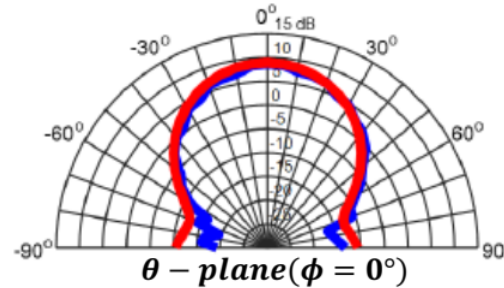


# Package Component Design Validation – Antennas



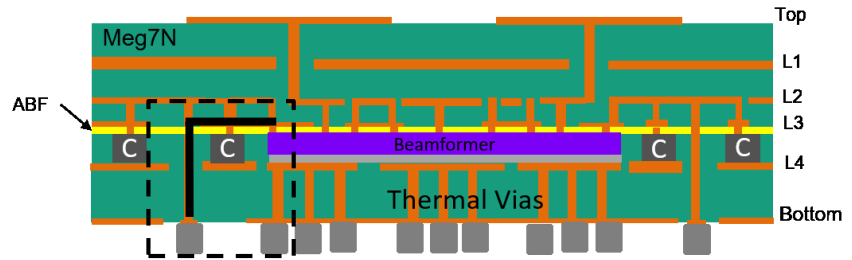
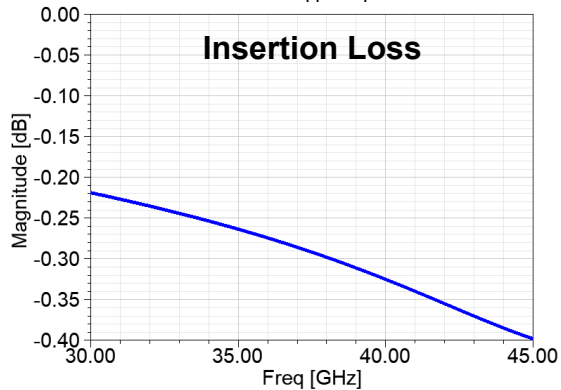
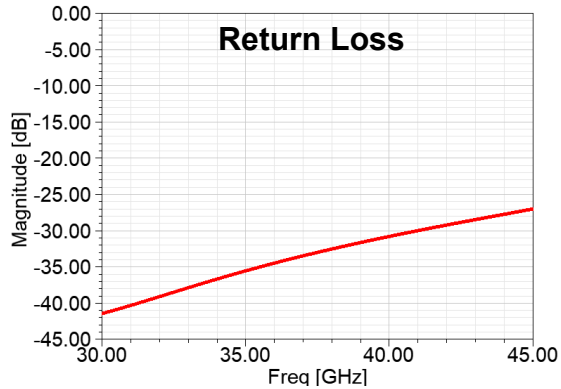
Fabricated antenna array

Parameter	Simulation	Measurement
Bandwidth	3 GHz (37.5 GHz - 40.5 GHz)	3.1 GHz (37 GHz - 40.6 GHz)
Peak Gain	9 dBi	8.8 dBi



Ivan Ndip

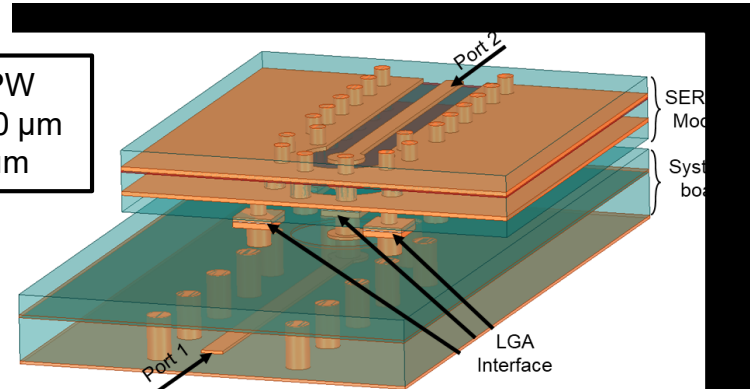
# Package Design Board-IC Interconnect



**Fig.:** Stackup of the SERENA modules

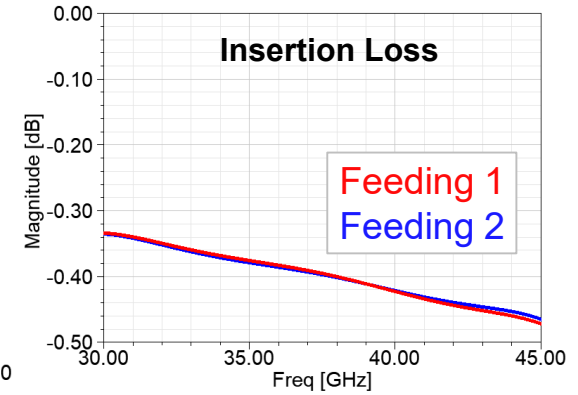
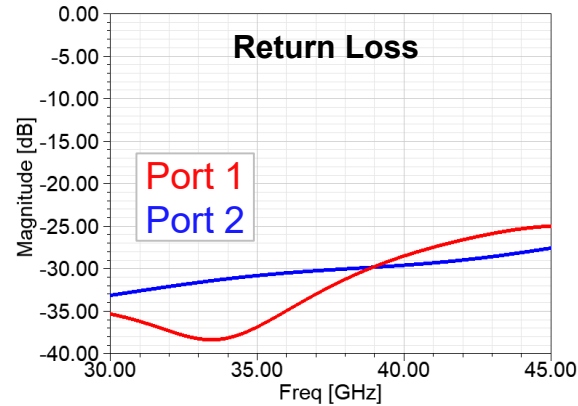
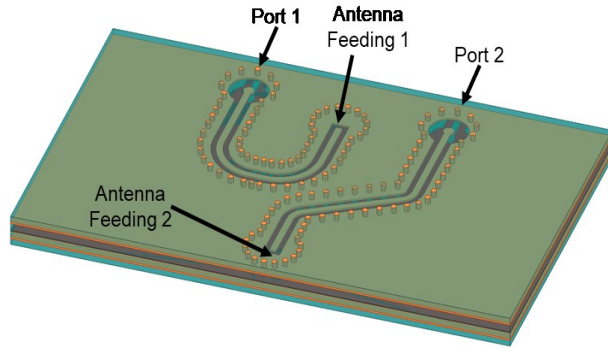
Module: GCPW  
 • Width: 110  $\mu\text{m}$   
 • Slot: 150  $\mu\text{m}$

System board: SL  
 • Width: 137  $\mu\text{m}$



**Fig.:** LGA transition from systemboard to SERENA embedded module

# Package Design IC-Antenna Interconnect



**Fig.:** Transmission lines from chip to antenna on layers L3 and L4 in the PCB Embedding module.

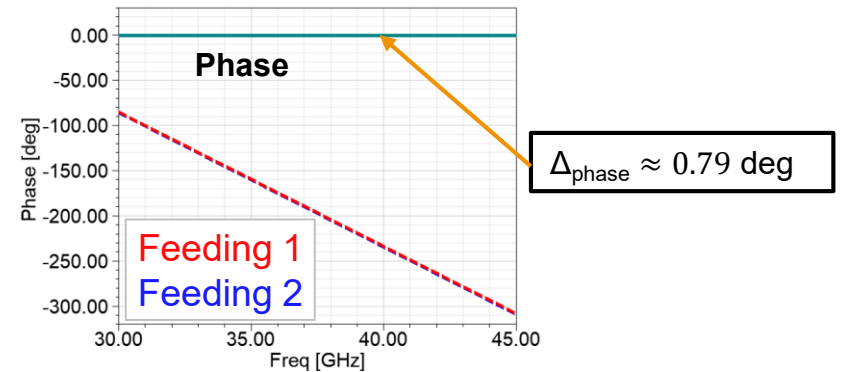
Layer 4: GCPW

- Width: 123  $\mu\text{m}$
- Slot: 100  $\mu\text{m}$

Layer 3: GCPW

- Width: 110  $\mu\text{m}$
- Slot: 150  $\mu\text{m}$

Total length:  $\approx 6 \text{ mm}$



# Fabrication – Embedding Process

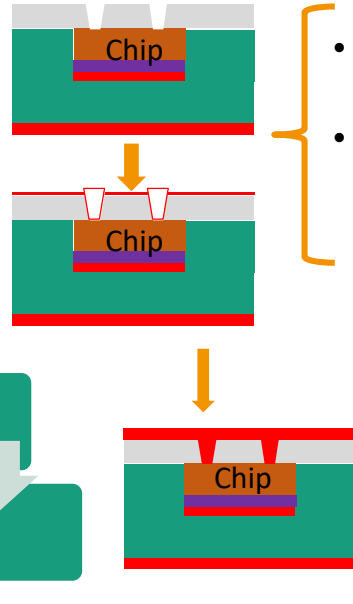
Die placement (sinter glue)

Embedding process  
Megtron 7N + ABF

Laser drilling

Sputtering process

Electro plating



- sputtering process (plating base):  
100nm TiW / 300nm Cu
- important: degassing of substrate prior  
to sputter process in order to ensure  
better Cu adhesion

electro plating: special  
electro plating bath with  
leveling characteristic  
("via filling")

# Fabrication - Lamination

- After embedding follows the build-up of the 3 further routing layers above the embedded layer
- Main process steps for each
  - lamination
  - laser drilling
  - metallization
  - structuring
  - pre-treatment for next lamination step

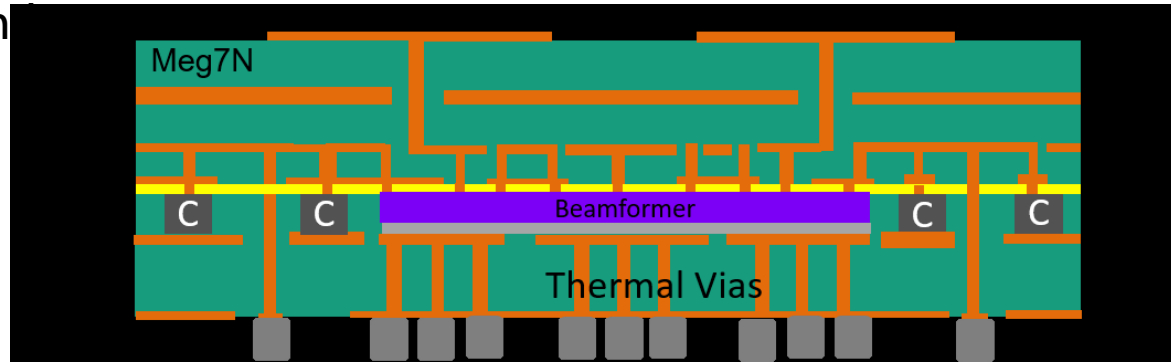
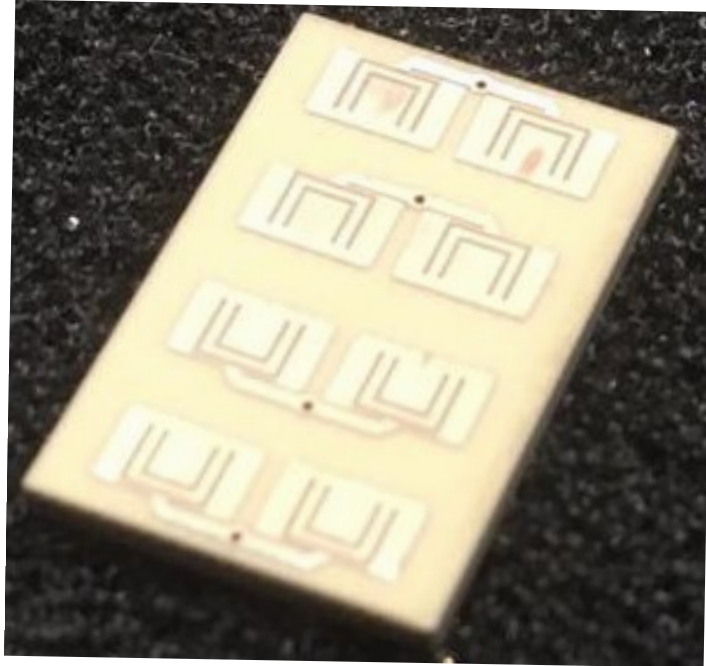
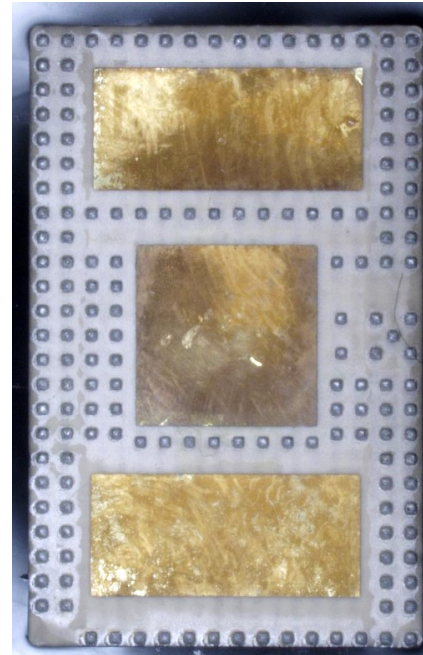


Fig.: Stackup of the SERENA module

# Fabricated Module

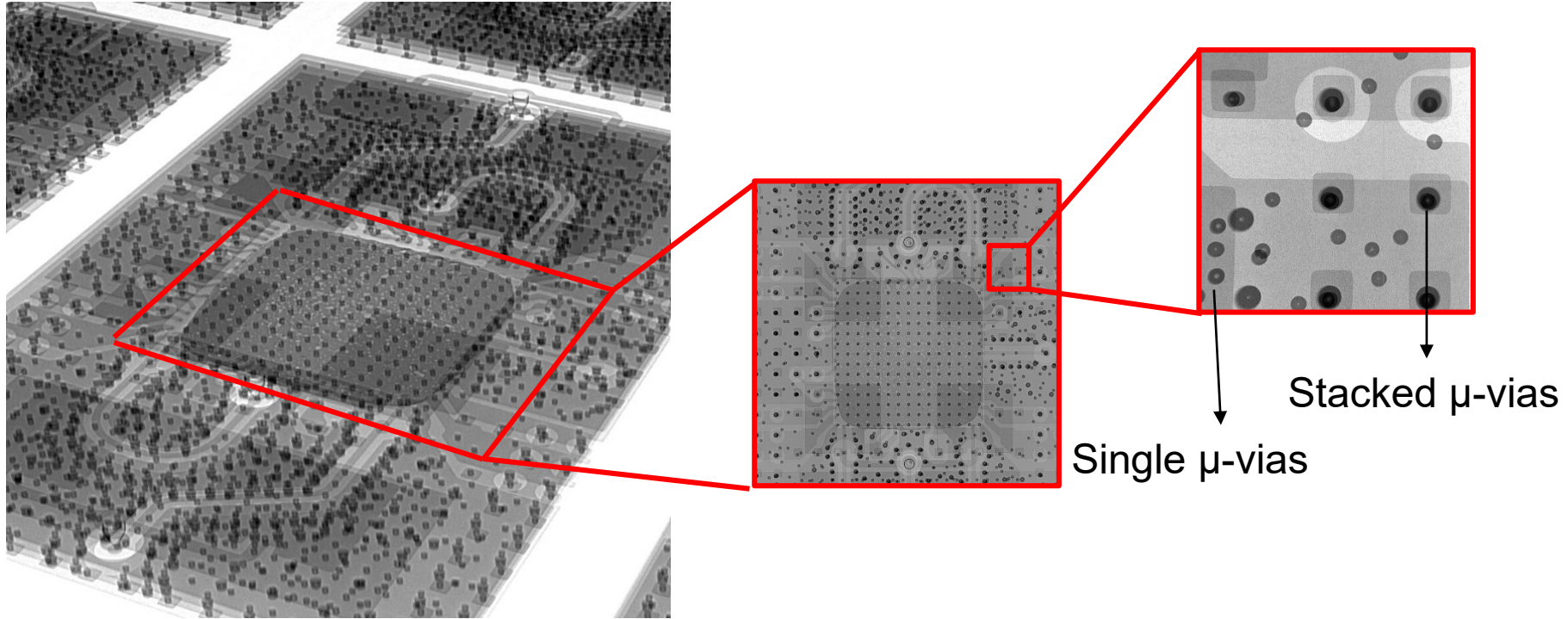


Top: Antenna layer



Bottom: LGA layer

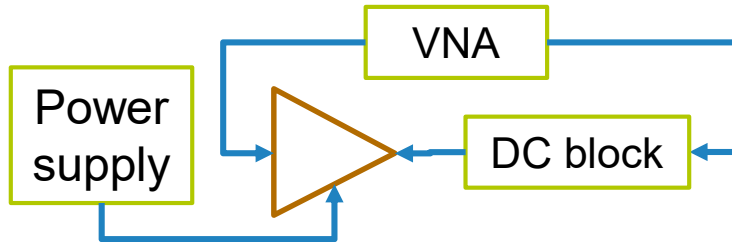
# Fabricated Modules - X-ray



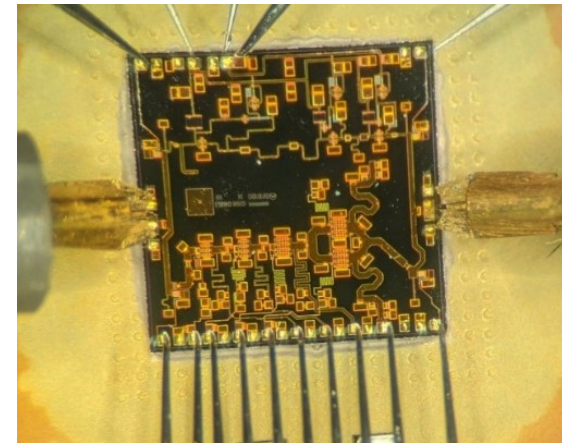
**Fig.:** X Ray - Fabricated Low power module.

# RF Characterization Set-up

- Development of measurement set-up for verification of critical manufacturing steps using Embedding test structure with GaN PA/LNA IC
- On-wafer characterisation
  - Connected to PNA E8361A (20 – 55 GHz)
  - Tests on bare dies and assembled ICs

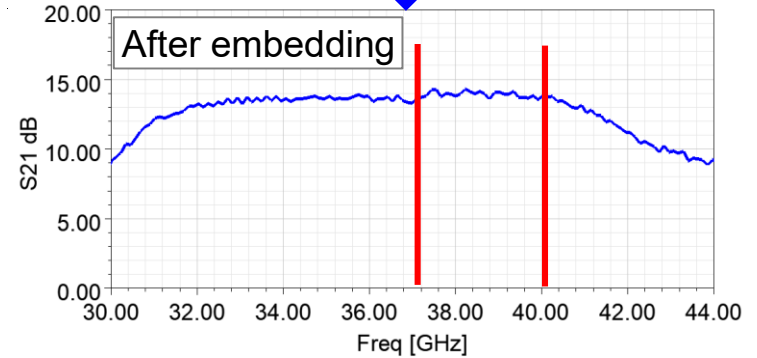
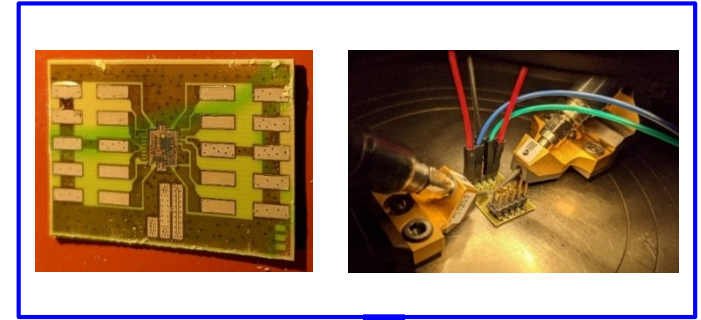
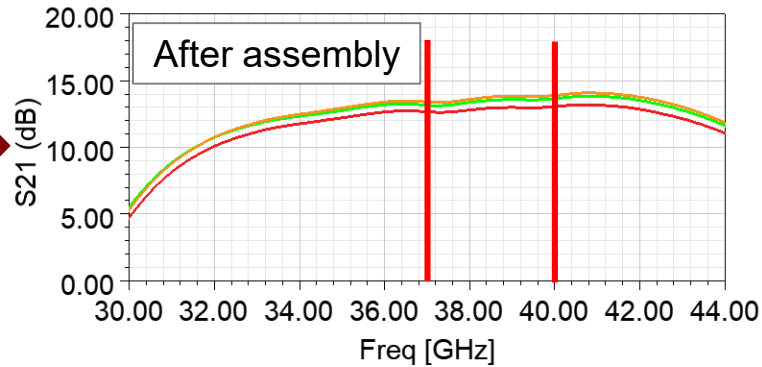
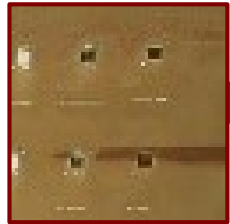
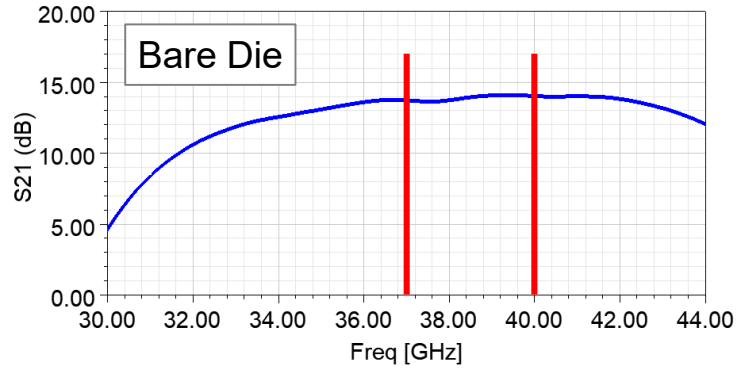


**Fig.:** Block diagramm of setup for RF measurements.

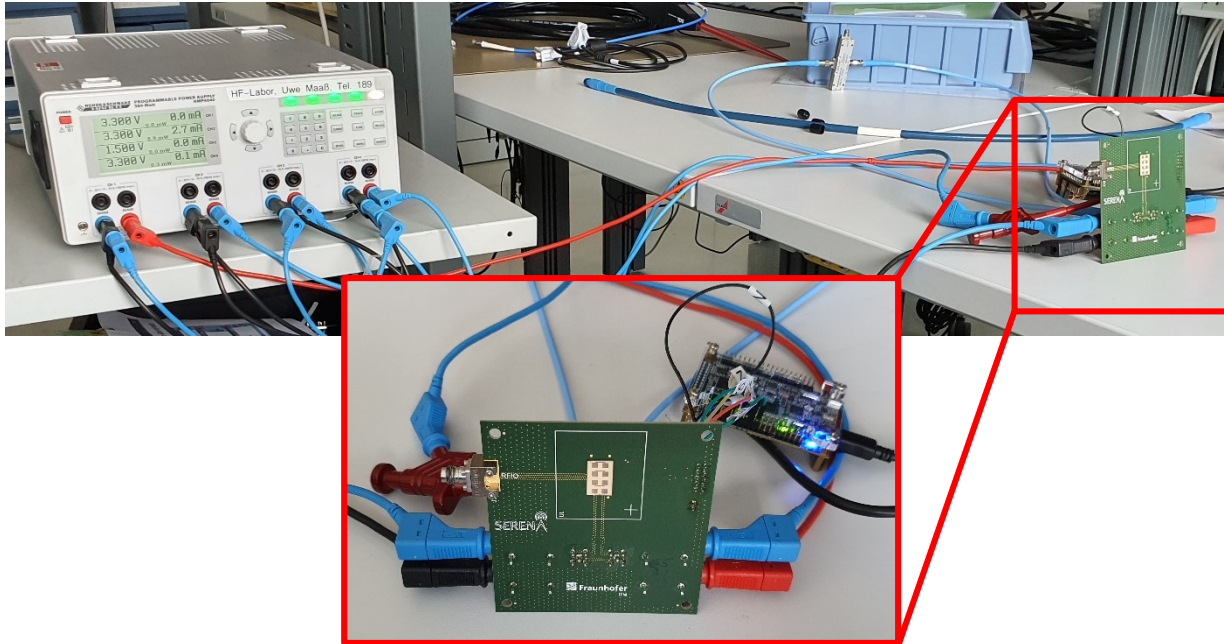




# RF Characterization – GaN LNA



# Evaluation of Fabricated Modules



**Fig.:** Measurement set-up of module mounted on test board including SPI interface

# Evaluation of Fabricated Modules

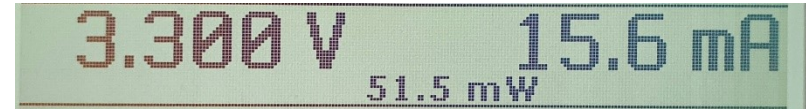
```
test 1/6
checking BEAM39PA status
this should print "status (0x4080): PON LOCK" after power on and "status (0x0000):" after rerunning this test
**
M1B1: status (0x4080): PON LOCK
**
clearing and checking BEAM39PA status, this should print "status (0x0000):"
cleared status registers
**
M1B1: status (0x0000):
**
resetting all BEAM39PAs to be in a known state: resetting SERENA system
press enter to continue, ctrl+c to stop test

2/6
testing register read/write of the BEAM39PA
This test uses the register PLL_CTRL_1. It tests for the default value, writes a value and reads it back.
testing BEAM39PA M1B1
reading default value:
* reading successful, default value correct
writing test value
reading test value:
* reading successful, value correct
writing back default value
press enter to continue, ctrl+c to stop test

3/6
testing BITE power (ADC), this should increase the current drawn at the VDD pin by probably >10mA
testing BEAM39PA M1B1
press enter to enable the ADC
* ADC enabled
press enter disable the ADC
press enter to continue, ctrl+c to stop test

4/6
testing RF power, VDDPA supply required.
Are the VDDPA pins and all VDD pins connected? Press "y" and enter for yes, just enter for no:
powering up the common channel and channel 0 in RX mode, current drawing should increase by roughly 120mA.
testing BEAM39PA M1B1
press enter to power common channel and channel 0 up
* M1B1: powered up press enter to power common channel and channel 0 down again
* M1B1: powered down
press enter to continue, ctrl+c to stop test

5/6
running MBIST tests of the BEAM39PAs, this should print "MBIST test successful"
* M1B1: MBIST test successful
press enter to continue, ctrl+c to stop test
```



**Fig.:** Results of mounted module measurement on test board

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If you need further information, please contact the coordinator:

TECHNIKON Forschungs- und Planungsgesellschaft mbH

Burgplatz 3a, 9500 Villach, AUSTRIA

Tel: +43 4242 233 55 Fax: +43 4242 233 55 77

E-Mail: [coordination@serena-h2020.eu](mailto:coordination@serena-h2020.eu)

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